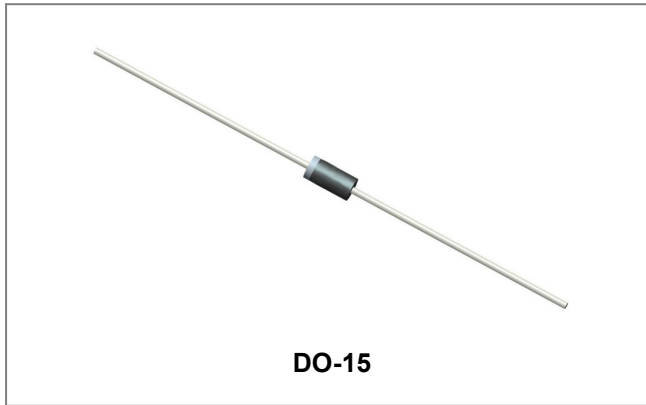


SB220 THRU SB260 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Green Products in Compliance with the RoHS Directive
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC DO-15 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.014 ounce, 0.40 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

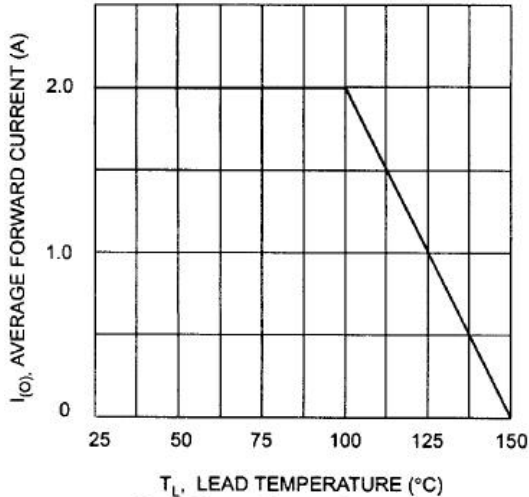
Characteristics	Symbol	SB220	SB230	SB240	SB250	SB260	Units
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	V
Maximum DC blocking voltage	V _{DC}						
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at T _L =100°C	I _(AV)	2.0					A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	50					A
Maximum instantaneous forward voltage at 2.0A	V _F	0.5			0.70		V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	5.0 10					mA
Typical junction capacitance (Note 1)	C _J	170			140		pF
Typical thermal resistance junction to lead	R _{θJL}	15					°C/W
Typical thermal resistance junction to ambient(Note 2)	R _{θJA}	50.0					°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +150					°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

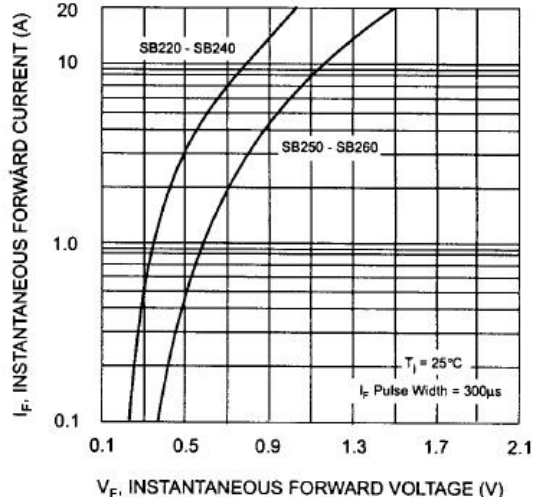
3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Ratings and Characteristics Curves



T_L , LEAD TEMPERATURE (°C)
Fig. 1 Forward Current Derating Curve



V_F , INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristics

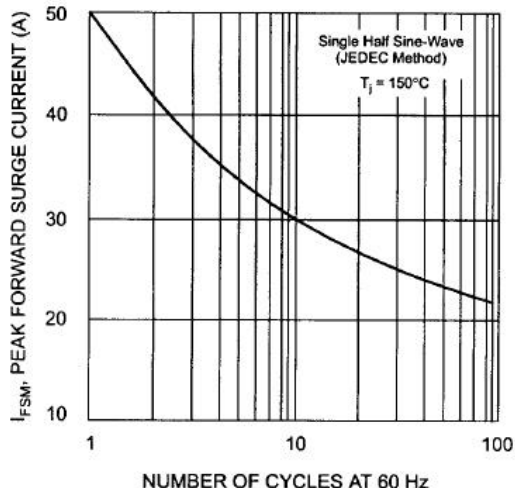


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

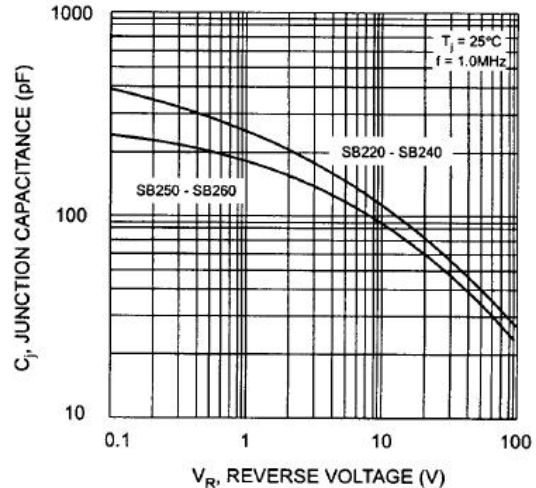


Fig. 4 Typical Junction Capacitance

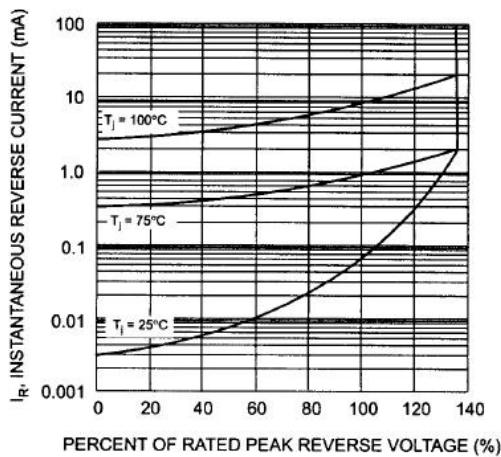
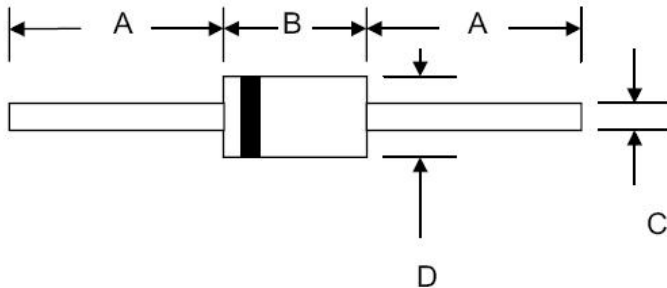


Fig. 5 Typical Reverse Characteristics

Mechanical Dimensions DO-15



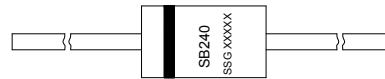
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	5.5	7.62	0.217	0.300
C	0.7	0.9	0.028	0.034
D	2.6	3.6	0.104	0.140

Ordering Information

Device	Package	Shipping
SB220 THRU SB260	DO-15(Pb-Free)	3000pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

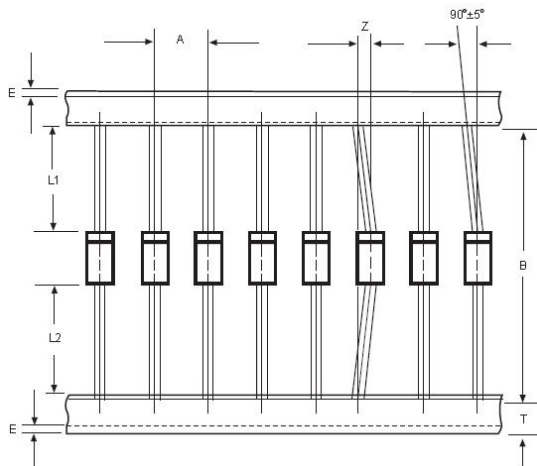


Where XXXXX is YYWWL

- SB = Device Type
- 2 = Forward Current (2A)
- 40 = Reverse Voltage (40V)
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DO-15



SYMBOL	Millimeters	
	Min.	Max.
A	4.50	5.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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